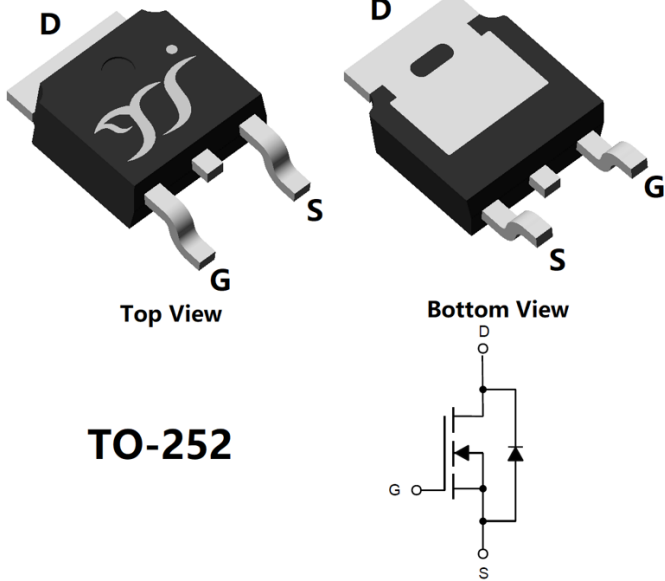


## N-Channel Enhancement Mode Field Effect Transistor



**TO-252**

### Product Summary

- $V_{DS}$  100V
- $I_D$  15A
- $R_{DS(ON)}$  (at  $V_{GS}=10V$ ) < 110mohm
- $R_{DS(ON)}$  (at  $V_{GS}=4.5V$ ) < 120mohm
- 100% EAS Tested
- 100%  $\nabla V_{DS}$  Tested

### General Description

- Trench Power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low  $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

### Applications

- DC-DC Converters
- Power management functions

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	$V_{DS}$	100	V
Gate-source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current	$I_D$	$T_C=25^\circ C$	15
		$T_C=100^\circ C$	9.5
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	60	A
Single Pulse Avalanche Energy <sup>B</sup>	$E_{AS}$	9	mJ
Total Power Dissipation	$P_D$	$T_C=25^\circ C$	28
		$T_C=100^\circ C$	11
Thermal Resistance Junction-to-Case <sup>C</sup>	$R_{\theta JC}$	4.4	$^\circ C/W$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ C$

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJD15N10A	F1/F2	YJD15N10A	2500	/	25000	13" reel



# YJD15N10A

RECOMMEND  
YJD12N10B  
FOR NEW DESIGN

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V	T <sub>J</sub> =25°C		1	μA
			T <sub>J</sub> =150°C		100	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.1	1.8	2.5	V
Static Drain-Source On-Resistance	R <sub>Ds(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =8A		95	110	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =8A		100	120	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =15A, V <sub>GS</sub> =0V		0.8	1.2	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				15	A
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>			1070		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHz		33		
Reverse Transfer Capacitance	C <sub>rss</sub>			30		
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =50V, I <sub>D</sub> =10A		26		nC
Gate-Source Charge	Q <sub>gs</sub>			5.4		
Gate-Drain Charge	Q <sub>gd</sub>			5.8		
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =10A, di/dt=100A/us		30.1		ns
Reverse Recovery Time	t <sub>rr</sub>			40		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =50V, R <sub>L</sub> =6.4Ω R <sub>GEN</sub> =3Ω		7		ns
Turn-on Rise Time	t <sub>r</sub>			24		
Turn-off Delay Time	t <sub>D(off)</sub>			24		
Turn-off fall Time	t <sub>f</sub>			31		

A. Pulse Test: Pulse Width ≤ 300μs, Duty cycle ≤ 2%.

B. T<sub>J</sub>=25°C, V<sub>DD</sub>=50V, V<sub>G</sub>=10V, L=0.5mH, I<sub>AS</sub>=6A

C. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design, while R<sub>θJA</sub> is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper



■ Typical Performance Characteristics

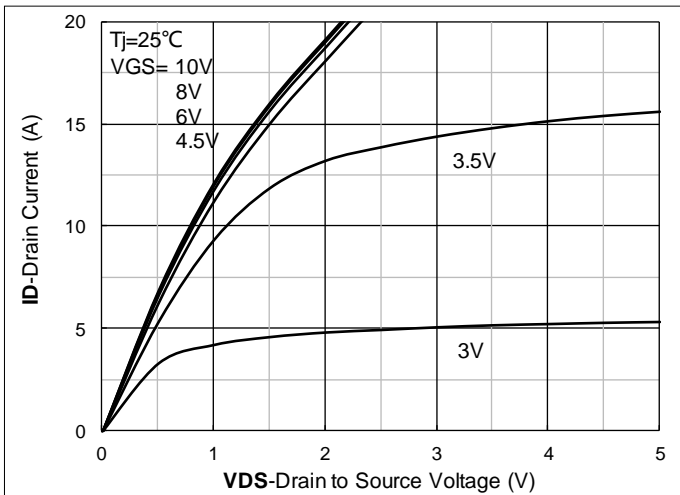


Figure 1. Output Characteristics

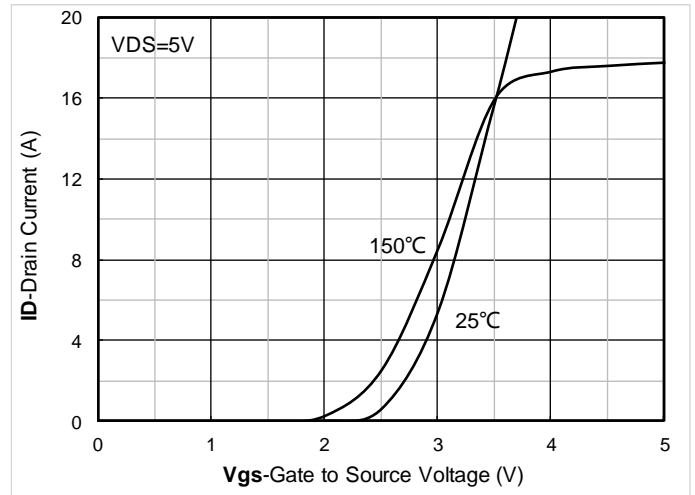


Figure 2. Transfer Characteristics

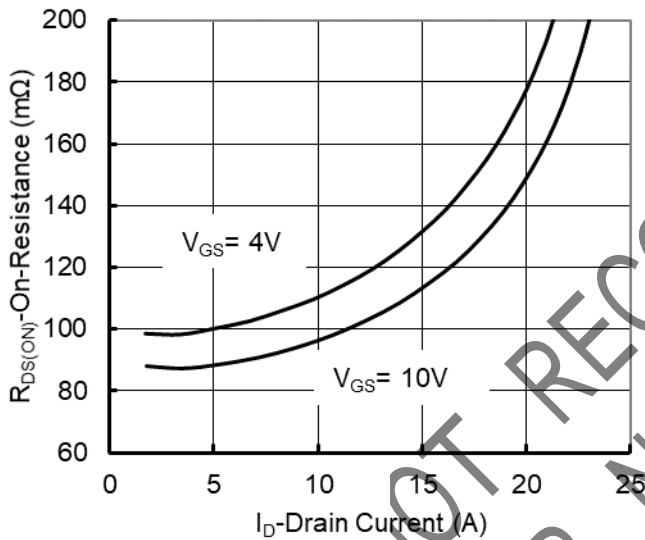


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

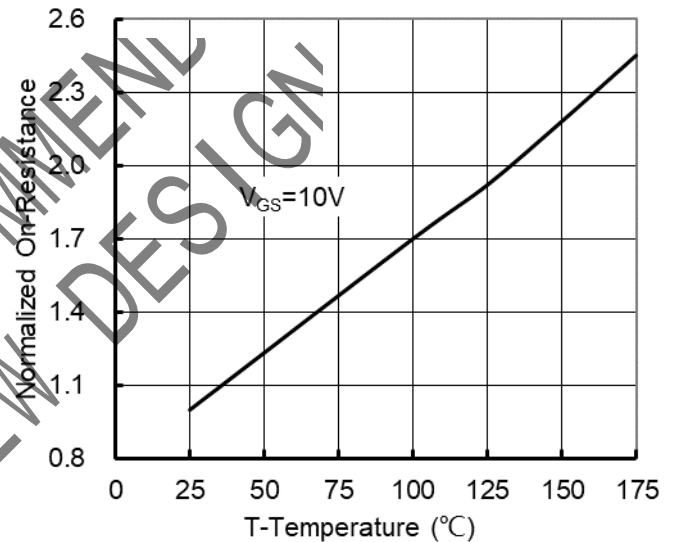


Figure 4. On-Resistance vs. Junction Temperature

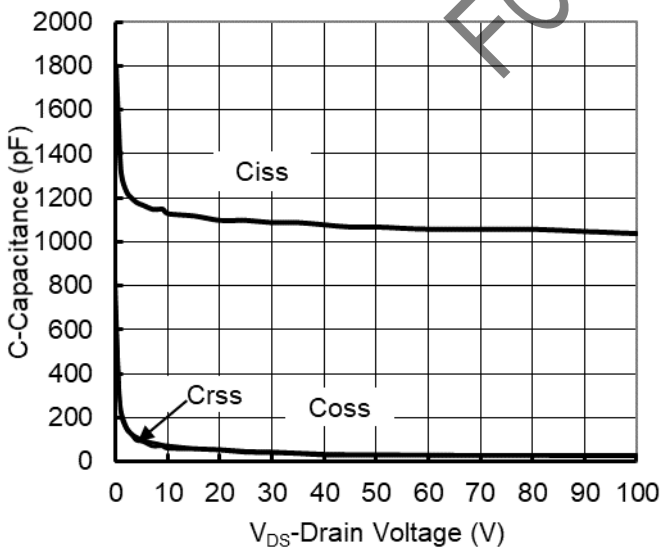


Figure 5. Capacitance Characteristics

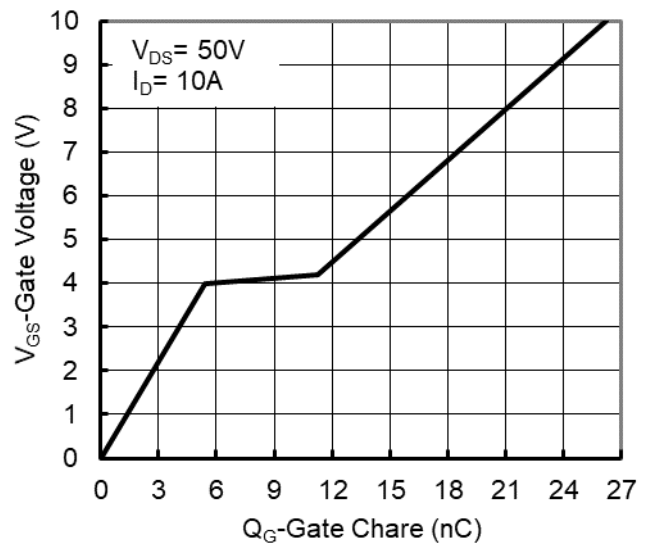


Figure 6. Gate Charge

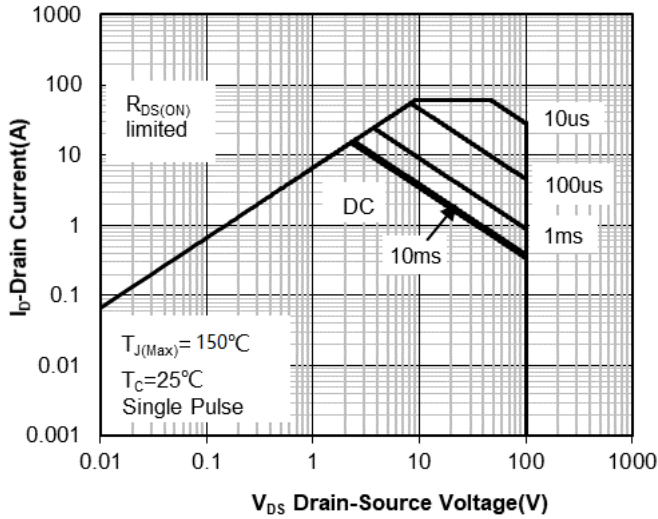


Figure 7. Safe Operation Area

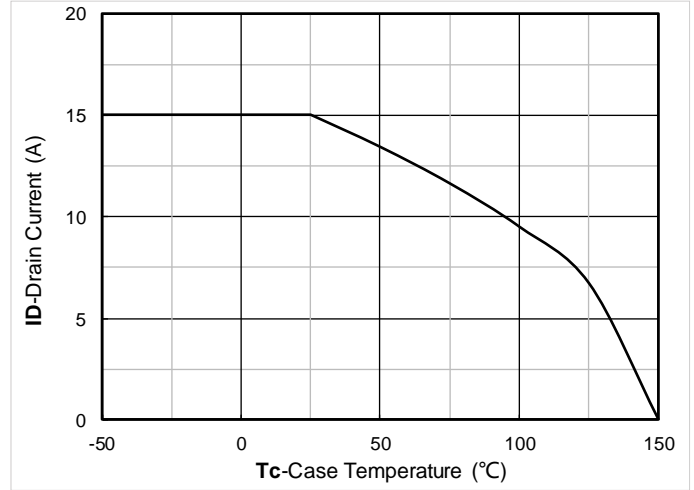


Figure 8. Maximum Continuous Drain Current vs Case Temperature

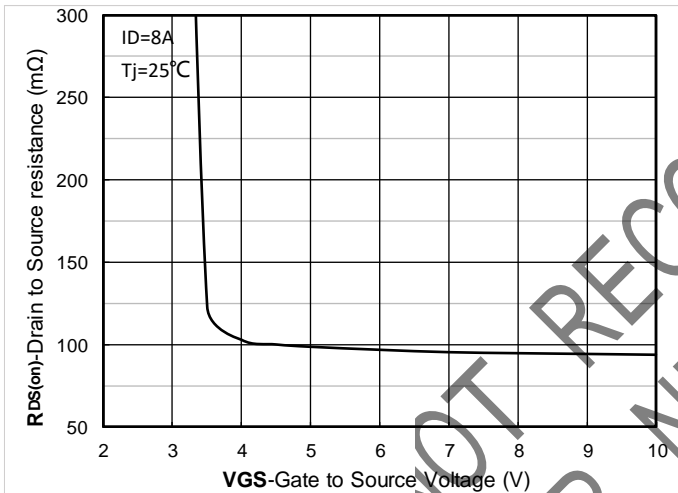


Figure 9. On-Resistance vs Gate to Source Voltage

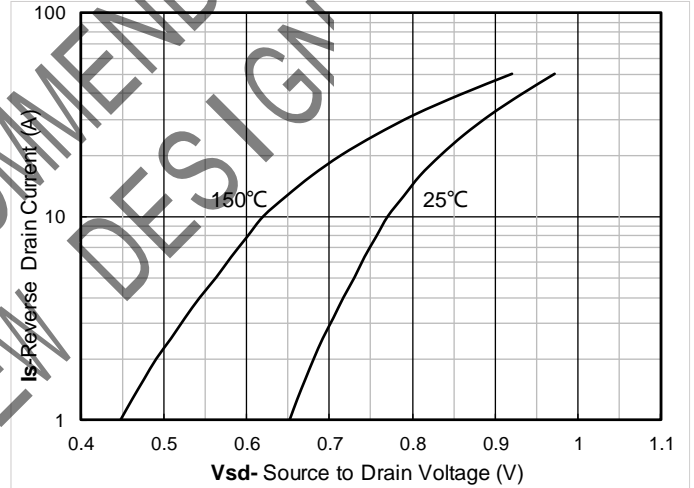


Figure 10. Forward characteristics of reverse diode

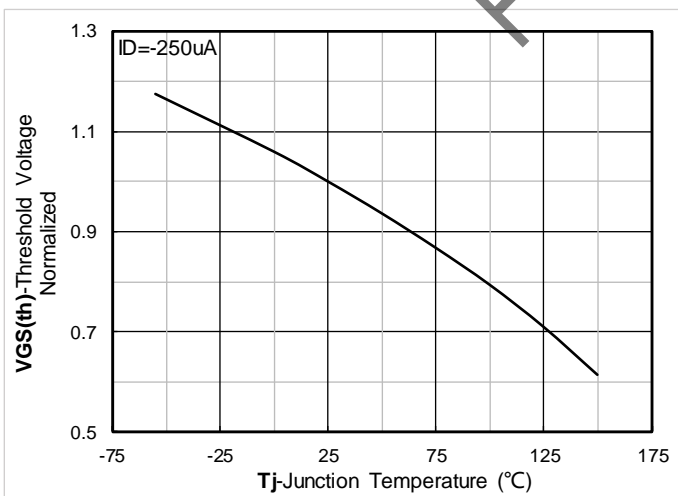


Figure 11. Normalized Threshold voltage

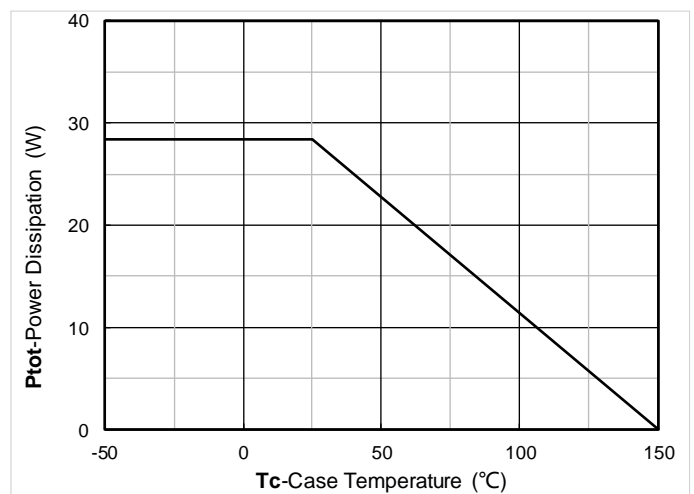


Figure 12. Power dissipation

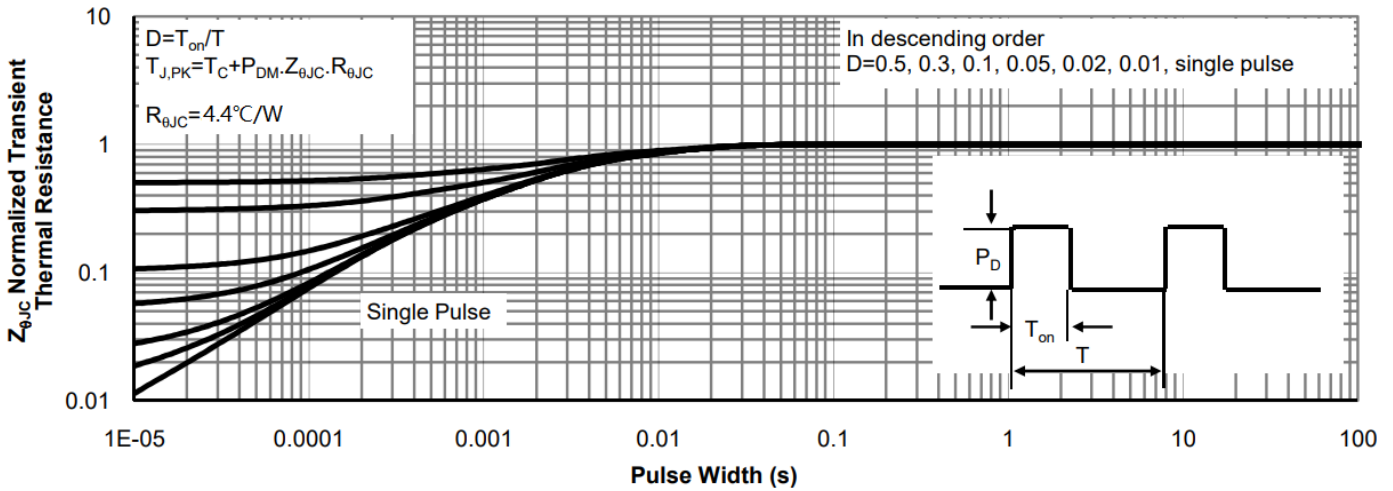
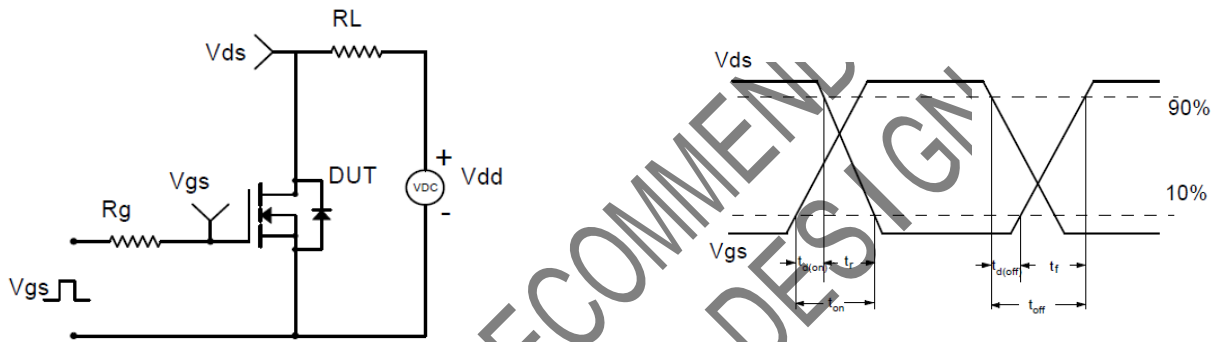
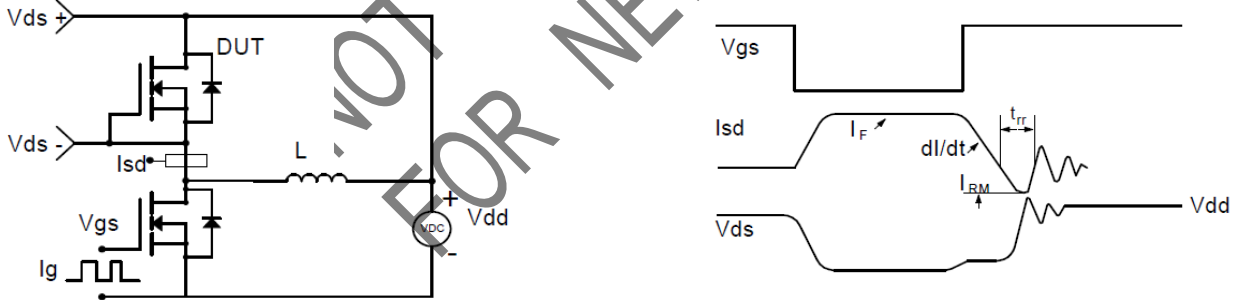


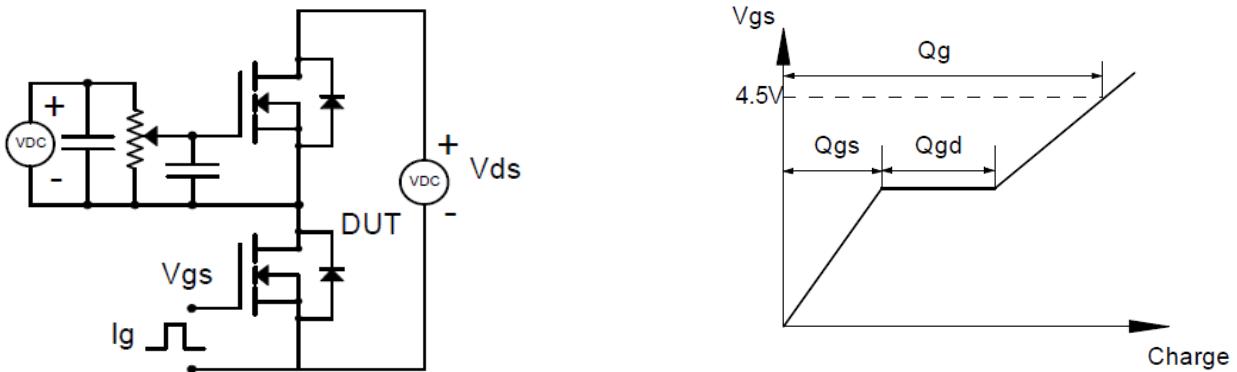
Figure 13. Normalized Maximum Transient Thermal Impedance



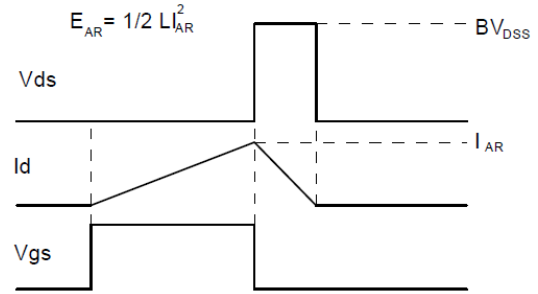
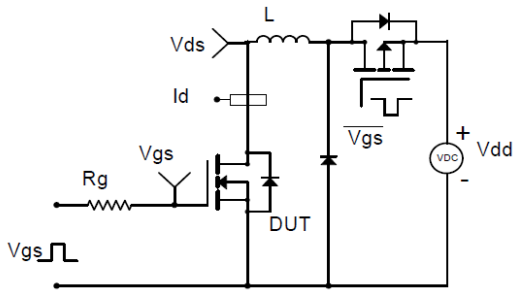
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

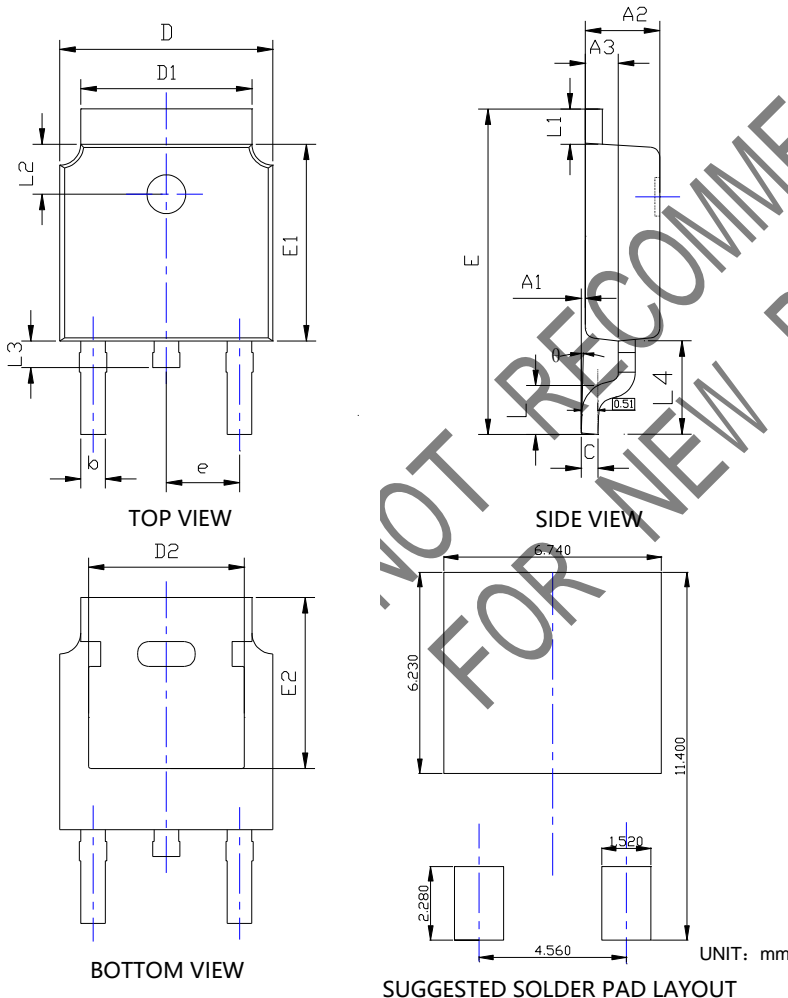


Gate Charge Test Circuit & Waveform



**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**

## TO-252-B Package information



SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A1	0.000	---	0.008	0.000	---	0.200
A2	0.087	0.091	0.094	2.200	2.300	2.400
A3	0.035	0.039	0.043	0.900	1.000	1.100
b	0.026	0.030	0.034	0.660	0.760	0.860
c	0.018	0.020	0.023	0.460	0.520	0.580
D	0.256	0.260	0.264	6.500	6.600	6.700
D1	0.203	0.209	0.215	5.150	5.300	5.450
D2	0.181	0.189	0.195	4.600	4.800	4.950
E	0.390	0.398	0.406	9.900	10.100	10.300
E1	0.236	0.240	0.244	6.000	6.100	6.200
E2	0.203	0.209	0.215	5.150	5.300	5.450
e	0.090BSC			2.286BSC		
L	0.049	0.059	0.069	1.250	1.500	1.750
L1	0.035	---	0.050	0.900	---	1.270
L2	0.055	---	0.075	1.400	---	1.900
L3	0.240	0.310	0.039	0.600	0.800	1.000
L4	0.114REF			2.900REF		
θ	0°	---	10°	0°	---	10°

**NOTE:**  
 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.  
 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.  
 3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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